

CAT93C46A/56A/66A/86A

1K/2K/4K/16K-Bit Serial E²PROM

FEATURES

- High Speed Operation: 1MHz
- **Low Power CMOS Technology**
- Wide Operating Voltage Range

 $V_{cc} = 4.5V \text{ to } 5.5V$

 $V_{cc}^{cc} = 2.7V \text{ to } 6.0V$

 V_{cc}^{cc} = 2.5V to 6.0V V_{cc}^{cc} = 1.8V to 6.0V

■ Self-Timed Write Cycle with Auto-Clear

- Hardware and Software Write Protection
- Power-Up Inadvertant Write Protection
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Commercial and Industrial Temperature Ranges
- x16 Serial Memory

DESCRIPTION

The CAT93C46A/56A/66A/86A is a 1K/2K/4K/16K-bit Serial E²PROM memory devices which are configured as registers of 16-bits. Each register can be written (or read) serially by using the DI (or DO) pin. The CAT93C46A/56A/66A/86A are manufactured using

Catalyst's advanced CMOS E²PROM floating gate technology. The devices are designed to endure 1,000,000 program/erase cycles and have a data retention of 100 years. The devices are available in 8-pin DIP or SOIC packages.

PIN CONFIGURATION

DIF	Pack	age	e (P)	SOIC Package (J)					
cs 🗆	- ₁ ∨	8	b vcc	NC (*PE)	• 1	8	D NC		
SK □	2	7	□ NC (*PE)	Vcc ⊏	2	7	□ GND		
DI 🗆	3	6	□ NC	cs 🗀	3	6	DO [C		
DO 🗆	4	5	GND	sk ⊏	4	5			

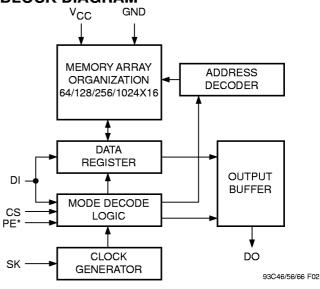
^{*}PE (only for 93C86A)

SOIC Package (S) SOIC Package (K) cs ぱ•1 8 □ vcc cs r**∃•**1 □ vcc 2 SK 🗀 NC (*PE) SK 🗀 NC (*PE) DIС ⊃ NC 3 6 h □ NC 3 6 DI L 5 h ☐ GND 5 DO [DO C j GND 93CXXA F01

PIN FUNCTIONS

Pin Name	Function
CS	Chip Select
SK	Clock Input
DI	Serial Data Input
DO	Serial Data Output
V _{CC}	+1.8V to 6.0V Power Supply
GND	Ground
PE*	Program Enable
NC	No Connect

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
Voltage on any Pin with Respect to Ground ⁽¹⁾ 2.0V to +V _{CC} +2.0V
V_{CC} with Respect to Ground –2.0V to +7.0V
Package Power Dissipation Capability (Ta = 25°C)1.0W
Lead Soldering Temperature (10 secs) 300°C
Output Short Circuit Current ⁽²⁾ 100 mA

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RELIABILITY CHARACTERISTICS

Symbol	Parameter	er Min. Max. Units		Units	Reference Test Method			
N _{END} (3)	Endurance	1,000,000		Cycles/Byte	MIL-STD-883, Test Method 1033			
T _{DR} (3)	Data Retention	100		Years	MIL-STD-883, Test Method 1008			
V _{ZAP} (3)	ESD Susceptibility	2000		Volts	MIL-STD-883, Test Method 3015			
I _{LTH} (3)(4)	Latch-Up	100		mA	JEDEC Standard 17			

D.C. OPERATING CHARACTERISTICS

 V_{CC} = +1.8V to +6.0V, unless otherwise specified.

			Limits			
Symbol	Parameter	Parameter Min. Typ. Max.		Units	Test Conditions	
Icc	Power Supply Current (Operating)			3	mA	$\begin{array}{l} DI = 0.0V, f_{SK} = 1 MHz \\ V_{CC} = 5.0V, CS = 5.0V, \\ Output Open \end{array}$
I _{SB}	Power Supply Current (Standby)			50	μА	CS = 0V
ILI	Input Leakage Current			2	μΑ	
llo	Output Leakage Current			10	μΑ	Vout = 0V to Vcc, CS = 0V
V _{IL1} V _{IH1}	Input Low Voltage Input High Voltage	-0.1 2		0.8 V _{CC} +1	V	4.5V≤V _{CC} <5.5V
V _{IL2} V _{IH2}	Input Low Voltage Input High Voltage	0 V _{CC} X0.7		V _{CC} X0.2 V _{CC} +1	V	1.8V≤V _{CC} <2.7V
V _{OL1} V _{OH1}	Output Low Voltage Output High Voltage	2.4		0.4	V	4.5V≤V _{CC} <5.5V I _{OL} = 2.1mA I _{OH} = -400μA
V _{OL2} V _{OH2}	Output Low Voltage Output High Voltage	V _{CC} -0.2		0.2	V	1.8V≤V _{CC} <2.7V I _{OL} = 1mA I _{OH} = -100μA

Note:

- (1) The minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5V, which may overshoot to V_{CC} +2.0V for periods of less than 20 ns.
- (2) Output shorted for no more than one second. No more than one output shorted at a time.
- (3) This parameter is tested initially and after a design or process change that affects the parameter.
- (4) Latch-up protection is provided for stresses up to 100 mA on address and data pins from −1V to V_{CC} +1V.

PIN CAPACITANCE

Symbol	Test	Test Max. Units		Conditions
C _{OUT} ⁽¹⁾	OUTPUT CAPACITANCE (DO)	5	pF	V _{OUT} =OV
C _{IN} ⁽¹⁾	INPUT CAPACITANCE (CS, SK, DI)	5	pF	V _{IN} =OV

Note:

(1) This parameter is tested initially and after a design or process change that affects the parameter.

INSTRUCTION SET

Instruction	Device Type	Start Bit	Opcode	Address x16	Data x16	PE ⁽¹⁾	Comments	
READ	93C46A 93C56A ⁽²⁾ 93C66A	1 1 1	10 10 10	A5-A0 A7-A0 A7-A0			Read Address AN-A0	
	93C86A	1	10	A9-A0		×		
ERASE	93C46A	1	11	A5-A0			Clear Address AN-A0	
	93C56A ⁽²⁾ 93C66A	1 1	11	A7-A0 A7-A0				
	93C86A		11	A9-A0		1		
WRITE	93C46A	1	01	A5-A0	D15-D0		Write Address AN-A0	
	93C56A ⁽²⁾		01	A7-A0	D15-D0			
	93C66A 93C86A	1 1	01 01	A7-A0 A9-A0	D15-D0 D15-D0	1		
EWEN	93C46A	1	00	11XXXX	3.030	- · ·	Write Enable	
	93C56A	1	00	11XXXXXX			Willo Eliabio	
	93C66A	1	00	11XXXXXX				
	93C86A	1	00	11XXXXXXXX		X		
EWDS	93C46A	1	00	00XXXX			Write Disable	
	93C56A	1	00	00XXXXXX				
	93C66A 93C86A	1 1	00	00XXXXXX 00XXXXXXXX		X		
EDAL						^	Ola All A -l-l	
ERAL	93C46A 93C56A	1 1	00	10XXXX 10XXXXXX			Clear All Addresses	
	93C66A		00	10XXXXXX				
	93C86A	i	00	10XXXXXXXX		1		
WRAL	93C46A	1	00	01XXXX	D15-D0		Write All Addresses	
	93C56A	1	00	01XXXXXX	D15-D0			
	93C66A	1	00	01XXXXXX	D15-D0			
	93C86A	1	00	01XXXXXXXX	D15-D0	1		

Note:

Only applicable to 93C86A
 Address bit A7 is "Don't Care" bit, but must be kept at either a "1" or "0" for Read, Write and Erase Commands.

A.C. CHARACTERISTICS

		Limits							
		V _{CC} = 1.8V-6V*		$V_{CC} = 2.7V - 6V$ $V_{CC} = 2.5V - 6V$					Test
SYMBOL	PARAMETER	Min.	Max.	Min.	Max.	Min.	Max.	UNITS	Conditions
tcss	CS Setup Time	200		100		50		ns	
tсsн	CS Hold Time	0		0		0		ns	
t _{DIS}	DI Setup Time	400		200		100		ns	
t _{DIH}	DI Hold Time	400		200		100		ns	
t _{PD1}	Output Delay to 1		1		0.5		0.25	μs	
t _{PD0}	Output Delay to 0		1		0.5		0.25	μs	C. 100pF
t _{HZ} ⁽¹⁾	Output Delay to High-Z		400		200		100	ns	C _L = 100pF
t _{EW}	Program/Erase Pulse Width		10		10		10	ms	
tcsmin	Minimum CS Low Time	1		0.5		0.25		μs	
tsĸнı	Minimum SK High Time	1		0.5		0.25		μs	
tsklow	Minimum SK Low Time	1		0.5		0.25		μs	
tsv	Output Delay to Status Valid		1		0.5		0.25	μs	
SK _{MAX}	Maximum Clock Frequency	DC	250	DC	500	DC	1000	KHZ	

^{*} Preliminary data for 93C56A/66A/86A.

NOTE:

⁽¹⁾ This parameter is tested initially and after a design or process change that affects the parameter.

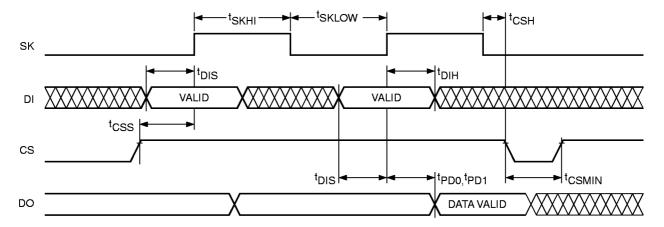
DEVICE OPERATION

The CAT93C46A/56A/66A/86A is a 1024/2048/4096/16384-bit nonvolatile memory intended for use with industry standard microprocessors. The CAT93C46A/56A/66A/86A is organized as registers of 16-bits. Therefore, seven 9-bit instructions for 93C46A; seven 11-bit instructions for 93C56A and 93C66A; seven 13-bit instructions for 93C86A, control the reading, writing and erase operations of the device. The CAT93C46A/56A/66A/86A operates on a single supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data from the device, or when checking the ready/busy status after a write operation. The ready/busy status can be determined after the start of a write operation by selecting the device (CS high) and polling the DO pin; DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. If necessary, the DO pin may be placed back into a high impedance state during chip select by shifting a dummy "1" into the DI pin. The DO pin will enter the high impedance state on the falling edge of the clock (SK). Placing the DO pin into the high impedance state is recommended in applications where the DI pin and the DO pin are to be tied together to form a common DI/O pin.

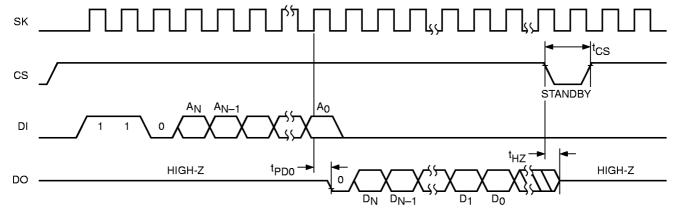
The format for all instructions sent to the device is a logical "1" start bit, a 2-bit (or 4-bit) opcode, 6-bit (93C46A)/8-bit (93C56A or 93C66A)/10-bit (93C86A) and for write operations a 16-bit data field.

Figure 1. Sychronous Data Timing



93C46/56/66A F03

Figure 2. Read Instruction Timing



93C46/56/66A F04

Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the CAT93C46A/56A/66A/86A will come out of the high impedance state and, after sending an initial dummy zero bit, will begin shifting out the data addressed (MSB first). The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay (tpDo or tpD1).

Write

After receiving a WRITE command, address and the data, the CS (Chip Select) pin must be deselected for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start the self clocking clear and data store cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of

the CAT93C46A/56A/66A/86A can be determined by selecting the device and polling the DO pin. Since this device features Auto-Clear before write, it is NOT necessary to erase a memory location before it is written into.

Erase

Upon receiving an ERASE command and address, the CS (Chip Select) pin must be deasserted for a minimum of 250ns (t_{CSMIN}). The falling edge of CS will start the self clocking clear cycle of the selected memory location. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C46A/56A/66A/86A can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical "1" state.

Figure 3. Write Instruction Timing

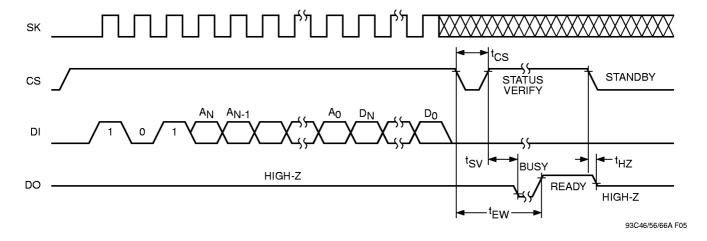
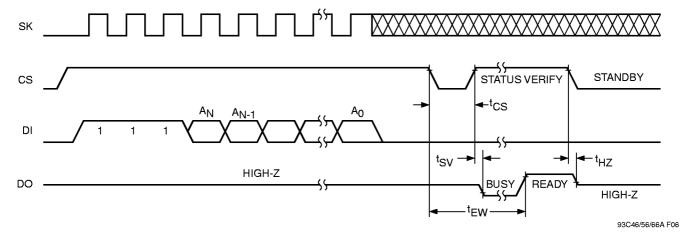


Figure 4. Erase Instruction Timing



Erase/Write Enable and Disable

The CAT93C46A/56A/66A/86A powers up in the write disable state. Any writing after power-up or after an EWDS (write disable) instruction must first be preceded by the EWEN (write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all write and clear instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/ disable status.

Erase All

Upon receiving an ERAL command, the CS (Chip Select) pin must be deselected for a minimum of 250ns (tcsmin). The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy

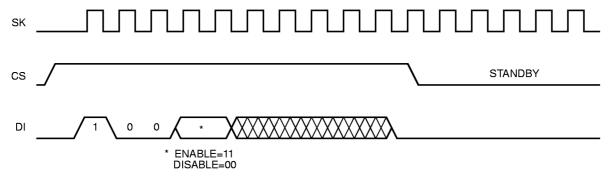
status of the CAT93C46A/56A/66A/86A can be determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits return to a logical "1" state.

Write All

Upon receiving a WRAL command and data, the CS (Chip Select) pin must be deselected for a minimum of 250ns (tcsmin). The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C46A/56A/66A/86A can be determined by selecting the device and polling the DO pin. It is not necessary for all memory locations to be cleared before the WRAL command is executed.

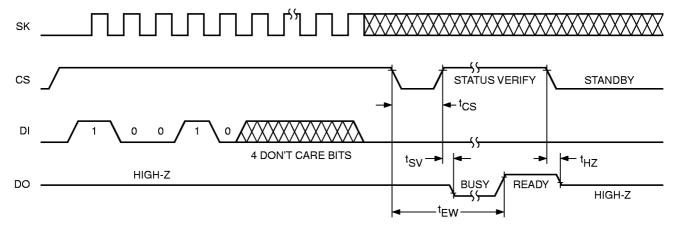
Note: This note is applicable only to 93C86A. The write, erase, write all and erase all instruction requires PE=1 for 93C86A. If PE is left floating, 93C86A is in program enabled mode.

Figure 5. EWEN/EWDS Instruction Timing



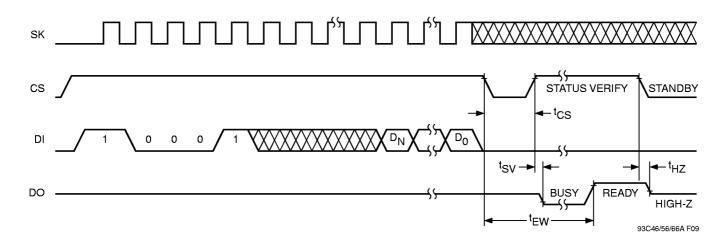
93C46/56/66A F07

Figure 6. ERAL Instruction Timing

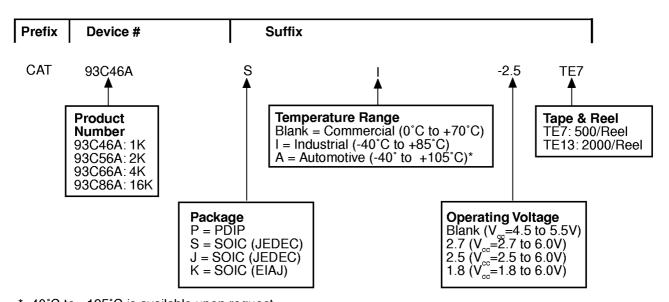


93C46/56/66A F08

Figure 7. WRAL Instruction Timing



ORDERING INFORMATION



* -40°C to +125°C is available upon request

93C46/56/66A F10

Notes:

(1) The device used in the above example is a 93C46ASI-2.5TE7 (SOIC, Industrial Temperature, 2.5 Volt to 6 Volt Operating Voltage, Tape & Reel)